

Silicon PNP Power Transistors

2SA1387

DESCRIPTION

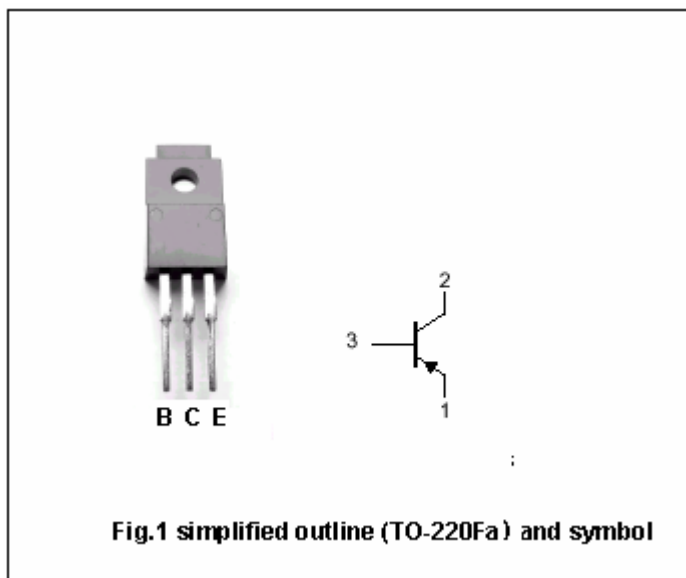
- With TO-220Fa package
- Low collector saturation voltage
- High speed switching time
- High DC current gain

APPLICATIONS

- High current switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-60	V
V _{CEO}	Collector-emitter voltage	Open base	-50	V
V _{EBO}	Emitter-base voltage	Open collector	-7	V
I _C	Collector current		-5	A
I _B	Base current		-1	A
P _C	Collector power dissipation	T _a =25°C	2	W
		T _C =25°C	20	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA ; I _B =0	-50			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-3A ; I _B =-0.075A		-0.15	-0.4	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-3A ; I _B =-0.075A		-0.8	-1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =-50V ; I _E =0			-1	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-7V ; I _C =0			-1	μA
h _{FE-1}	DC current gain	I _C =-1A ; V _{CE} =-1V	150		400	
h _{FE-2}	DC current gain	I _C =-3A ; V _{CE} =-1V	70			
f _T	Transition frequency	I _C =-1A ; V _{CE} =-4V		80		MHz
C _{ob}	Collector output capacitance	I _E =0 ; V _{CE} =-10V ; f=1MHz		200		pF

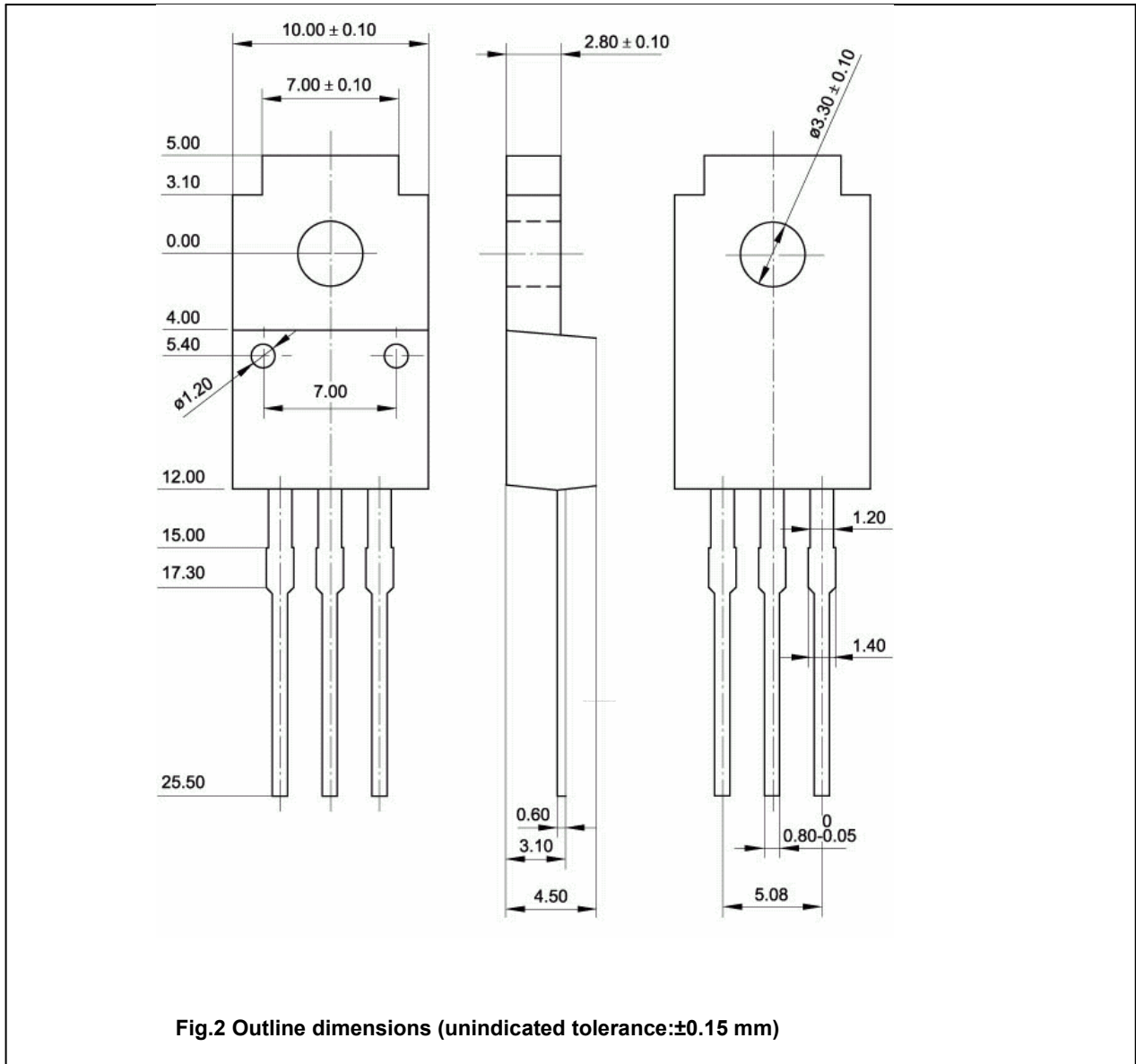
Switching times

T _{on}	Turn-on time	I _{B1} =-I _{B2} =-0.075A V _{CC} =-30V ; R _L =10Ω		0.2		μs
t _s	Storage time			1.0		μs
t _f	Fall time			0.2		μs

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PACKAGE OUTLINE



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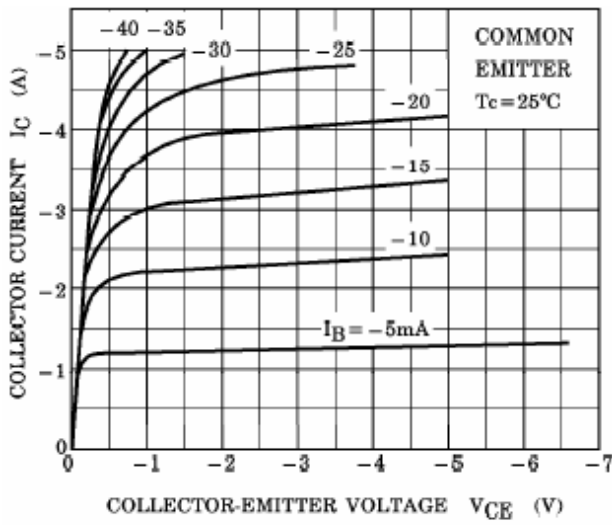


Fig.3 Static Characteristic

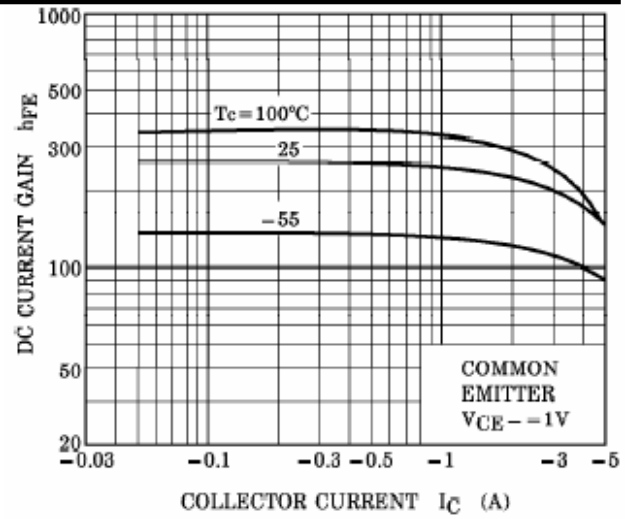


Fig.4 DC current Gain

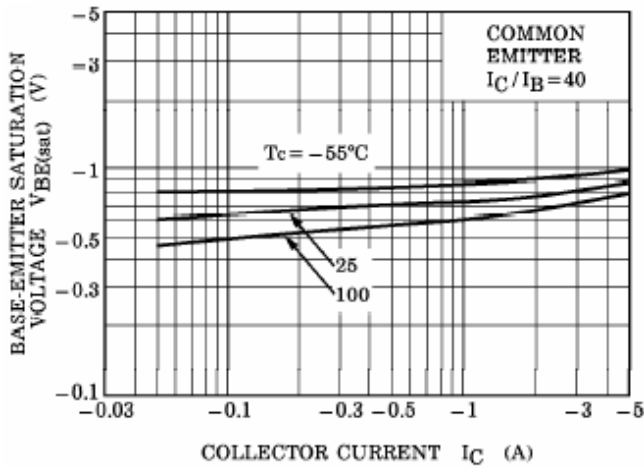


Fig.5 Base-Emitter Saturation Voltage

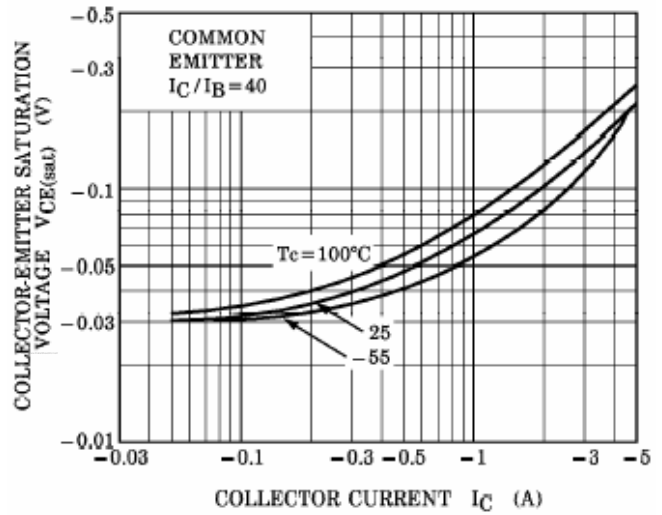


Fig.6 Collector-Emitter Saturation Voltage

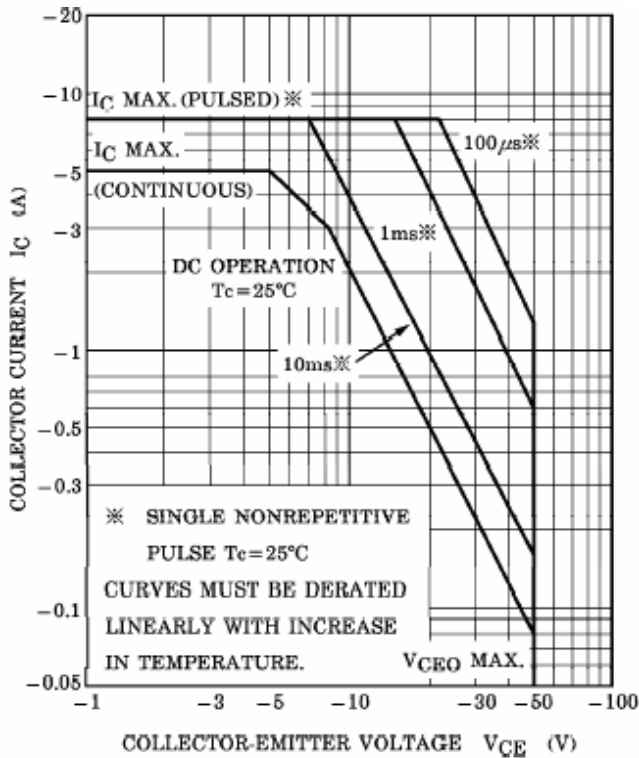


Fig.7 Safe Operating Area